

2/1/02 #25/D
2/19/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Enomoto, et al.

Docket No.: TIJ-24816

Serial No.: 09/019,087

Art Unit: 1765

Filed: 02/05/1998

Examiner: Perez Ramos, V

For: Manufacturing Method of Semiconductor IC Device

AMENDMENT UNDER 37 CFR 1.115

Assistant Commissioner for Patents
Washington, D. C. 20231

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MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(A) I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

William B. Kempler, Reg. No. 28,228

1/10/02
Date

Sir:

In response to the Office Action dated September 10, 2001, in connection with the above-identified patent application, please make the following amendments. They are respectfully submitted as a full and complete response to that Action.

IN THE CLAIMS:

Please amend claims 1-3 as follows:

- D.
1. (Four Times Amended) A manufacturing method of a semiconductor IC device, comprising the following steps :
forming an insulating film on a semiconductor substrate or SOI substrate;
forming a first mask film on the insulating film;